



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT
SCHOTTKY BARRIER DIODE

VOLTAGE 30 Volts CURRENT 0.1 Ampere

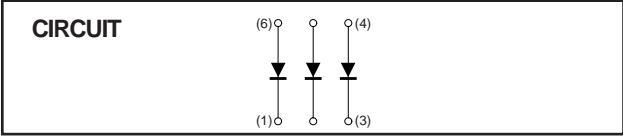
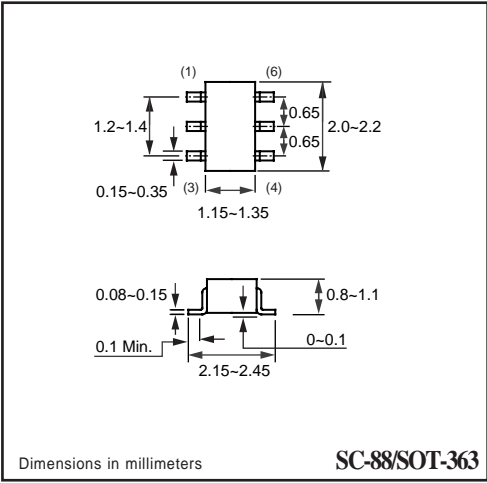
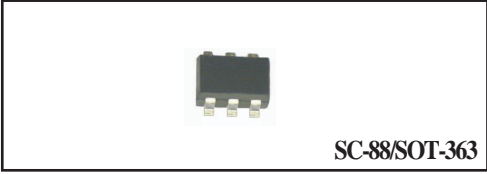
CH531UGP

APPLICATION
* High speed switching

FEATURE
* Small surface mounting type. (SC-88/SOT-363)
* Low VF and low IR
* Three diodes in parallel installation

CONSTRUCTION
* Silicon epitaxial planar

MARKING
* BZ



MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH531UGP	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	30	Volts
Maximum RMS Voltage	VRMS	21	Volts
Maximum DC Blocking Voltage	VDC	30	Volts
Maximum Average Forward Rectified Current	IO	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	IFSM	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF
Maximum Operating Temperature Range	TJ	+125	°C
Storage Temperature Range	TSTG	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH531UGP	UNITS
Maximum Instantaneous Forward Voltage at IF= 100mA	VF	0.43	Volts
Maximum Average Reverse Current at VR= 10V	IR	30	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.
2. ESD sensitive product handling required.

RATING CHARACTERISTIC CURVES (CH531UGP)

FIG. 1 - FORWARD CHARACTERISTICS

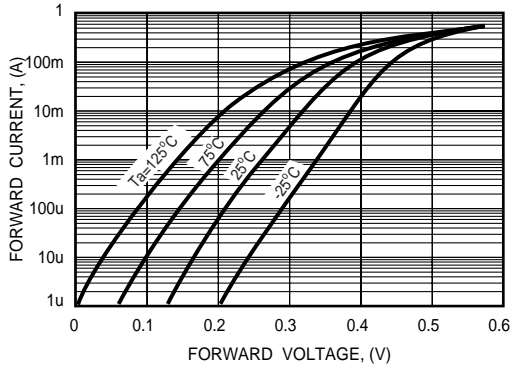


FIG. 2 - REVERSE CHARACTERISTICS

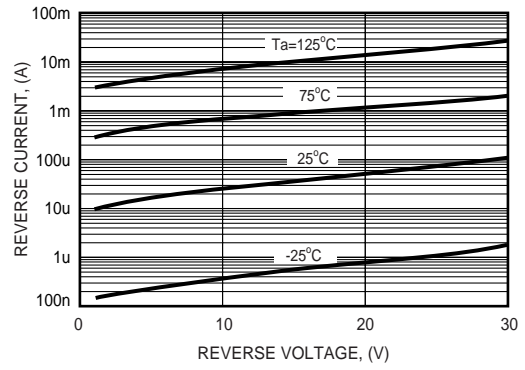


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

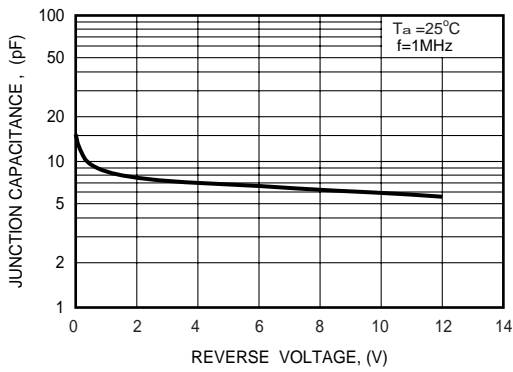


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

